

REPLY



To: Examiner of the Patent Office

1. Identification of the International Application

PCT/JP03/13074

2. Applicant

Name: CANON KABUSHIKI KAISHA

Address: 3-30-2, Shimomaruko, Ohta-ku, Tokyo
146-8501 Japan

Country of Nationality: JAPAN

Country of Residence: JAPAN

3. Agent

Name: TAKANASHI, Norimichi



Address: No. 602, Fuji Bldg., 2-3, Marunouchi 3-chome,
Chiyoda-ku, Tokyo 100-0005 Japan

4. Date of Notification: 03.08.2004

5. Subject Matter of Reply:

This is a reply to the first Written Opinion mailed August 3,
2004.

The Applicant has amended Claims 1 and 2 with the Amendment
separately filed.

According to the present invention, in order to prevent variance

in conductivity and resistivity of a substrate when an unpurified metallurgical grade (metal grade) silicon containing B or P in an amount of approximately tens of ppmw is used as a material, B or Al of an amount which does not lower the crystallinity is added to produce a substrate having resistivity of $300 \Omega \cdot \text{cm}$ or less. A characteristic of the present invention is that a large quantity of B or Al, which is not affected by an amount of P or B contained in a material, is added into a melt.

D1 discloses that plate-shaped metal-grade silicon contains B or Al. However, D1 does not have the description that a predetermined amount of B or Al is intentionally added into molten metal-grade silicon.

D2 discloses that B or Al is added to molten silicon and directional solidification is performed. However, the melt is a melt of electronic grade silicon, not a melt of metal grade silicon as used in the present invention.

AMENDMENT

(Amendment based upon the provision of Article 11 of said Law)



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Name: (10280) TAKANASHI, Norimichi



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Chiyoda-ku, Tokyo 100-0005 Japan

4. Item to be amended: Claims

5. Subject Matter of Amendment

Claims 1 and 2 have been changed their category from "a polycrystalline silicon substrate for a solar cell" to --a method of producing a polycrystalline silicon substrate for a solar cell--.

6. List of Attached Document

1) A replacement sheet of page 42

CLAIMS

1. (Amended) A method of producing a polycrystalline silicon substrate for a solar cell, comprising the steps of:

5 performing one-direction solidification on a melt prepared by melting metallurgical grade silicon to form a polycrystalline silicon ingot;

slicing the polycrystalline silicon ingot to obtain a base; and

10 growing a high purity polycrystalline silicon layer on a surface of the base,

wherein the melt is prepared by adding B to molten metallurgical grade silicon at an amount of $2 \times 10^{18} \text{ cm}^{-3}$ to $5 \times 10^{19} \text{ cm}^{-3}$ based on a concentration.

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2. (Amended) A method of producing a polycrystalline silicon substrate for a solar cell, comprising the steps of:

performing one-direction solidification on a
20 melt prepared by melting metallurgical grade silicon to form a polycrystalline silicon ingot;

slicing the polycrystalline silicon ingot to obtain a base; and

growing a high purity polycrystalline silicon
25 layer on a surface of the base,

wherein the melt is prepared by adding Al to molten metallurgical grade silicon at an amount of $1 \times 10^{19} \text{ cm}^{-3}$ to $1 \times 10^{21} \text{ cm}^{-3}$ based on a concentration.